

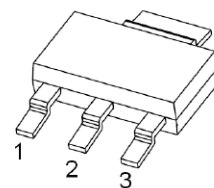
SOT-223 Plastic-Encapsulate Transistors

CZT32C TRANSISTOR (PNP)

FEATURES

- Complementary to CZT31C
- Power amplifier applications up to 3.0 amps.

SOT-223



1. BASE
2. COLLECTOR
3. EMITTER

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Power Dissipation	1	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-65~150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-30\text{mA}, I_B=0$	-100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-3\text{mA}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-100\text{V}, I_E=0$			-200	μA
Base cut-off current	I_{CEO}	$V_{CE}=-60\text{V}, I_B=0$			-300	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-1	mA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=-4\text{V}, I_C=-1\text{A}$	25			
	$h_{FE(2)}^*$	$V_{CE}=-4\text{V}, I_C=-3\text{A}$	10		100	
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=-3.0\text{A}, I_B=-375\text{mA}$			-1.2	V
Base-emitter voltage	$V_{BE(on)}^*$	$V_{CE}=-4\text{V}, I_C=-3\text{A}$			-1.8	V
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-500\text{mA}, f=1\text{MHz}$	3			MHz

* Pulsed , 2%D.C.